

General Description

The 5972A uses advanced trench technology and design to provide excellent RDS(ON). It can be used in a wide variety of applications.

Features

- Fast switching
- 100% avalanche tested
- 175°C Operating Temperature
- RoHS Compliant

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	70	V
V_{GS}	Gate-Source Voltage	± 25	V
$I_D@T_C=25^\circ C$	Continuous Drain Current	90	A
$I_D@T_C=100^\circ C$	Continuous Drain Current	72	A
I_{DM}	Pulsed Drain Current	270	A
EAS	Single Pulse Avalanche Energy	360	mJ
$P_D@T_C=25^\circ C$	Total Power Dissipation	200	W
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 175	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient	---	62.5	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-case	---	1.0	$^\circ C/W$

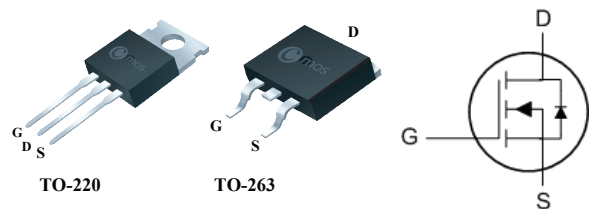
Product Summary

BVDSS	RDSON	ID
70V	9m Ω	90A

Applications

- LED power controller
- DC-DC & DC-AC converters
- High current, high speed switching
- Solenoid and relay drivers
- Motor control, Audio amplifiers

TO-220 Pin Configuration



Type	Package	Marking
CMP5972A	TO-220	CMP5972A
CMB5972A	TO-263	CMB5972A

Electrical Characteristics (T_J=25°C , unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	70	---	---	V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V , I _D =25A	---	---	9	mΩ
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =6V , I _D =20A	---	---	17	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	2	---	4	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =60V , V _{GS} =0V	---	---	1	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±25V , V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =10V , I _D =10A	---	25	---	S
R _g	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz	---	1.8	---	Ω
Q _g	Total Gate Charge	I _D =30A	---	95	---	nC
Q _{gs}	Gate-Source Charge	V _{DS} =30V	---	17	---	
Q _{gd}	Gate-Drain Charge	V _{GS} =10V	---	25	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =30V , I _D =2A	---	16	---	ns
T _r	Rise Time	R _L =15Ω	---	12	---	
T _{d(off)}	Turn-Off Delay Time	R _G =2.5Ω	---	53	---	
T _f	Fall Time	V _{GS} =10V	---	14	---	
C _{iss}	Input Capacitance	V _{DS} =25V , V _{GS} =0V , f=1MHz	---	3500	---	pF
C _{oss}	Output Capacitance		---	310	---	
C _{rss}	Reverse Transfer Capacitance		---	221	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _G =V _D =0V , Force Current	---	---	90	A
I _{SM}	Pulsed Source Current		---	---	270	A
V _{SD}	Diode Forward Voltage	V _{GS} =0V , I _S =45A , T _J =25°C	---	---	1.2	V

Note :

This product has been designed and qualified for the consumer market.
 Cmos assumes no liability for customers' product design or applications.
 Cmos reserves the right to improve product design ,functions and reliability without notice.